

FIG. 1

FIG. 2A

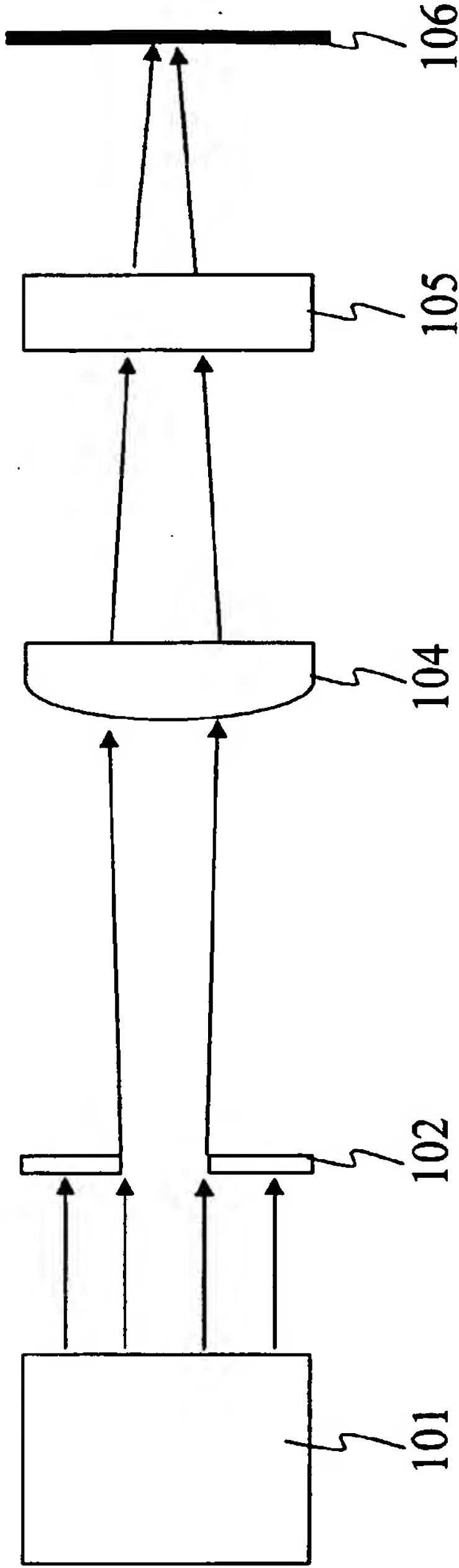
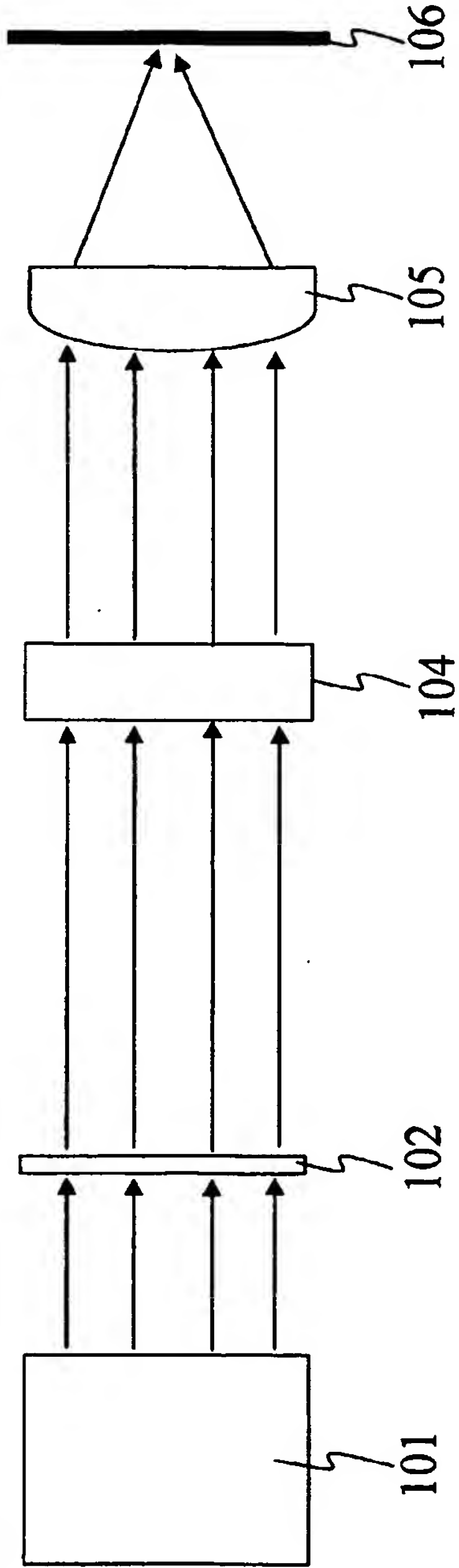


FIG. 2B



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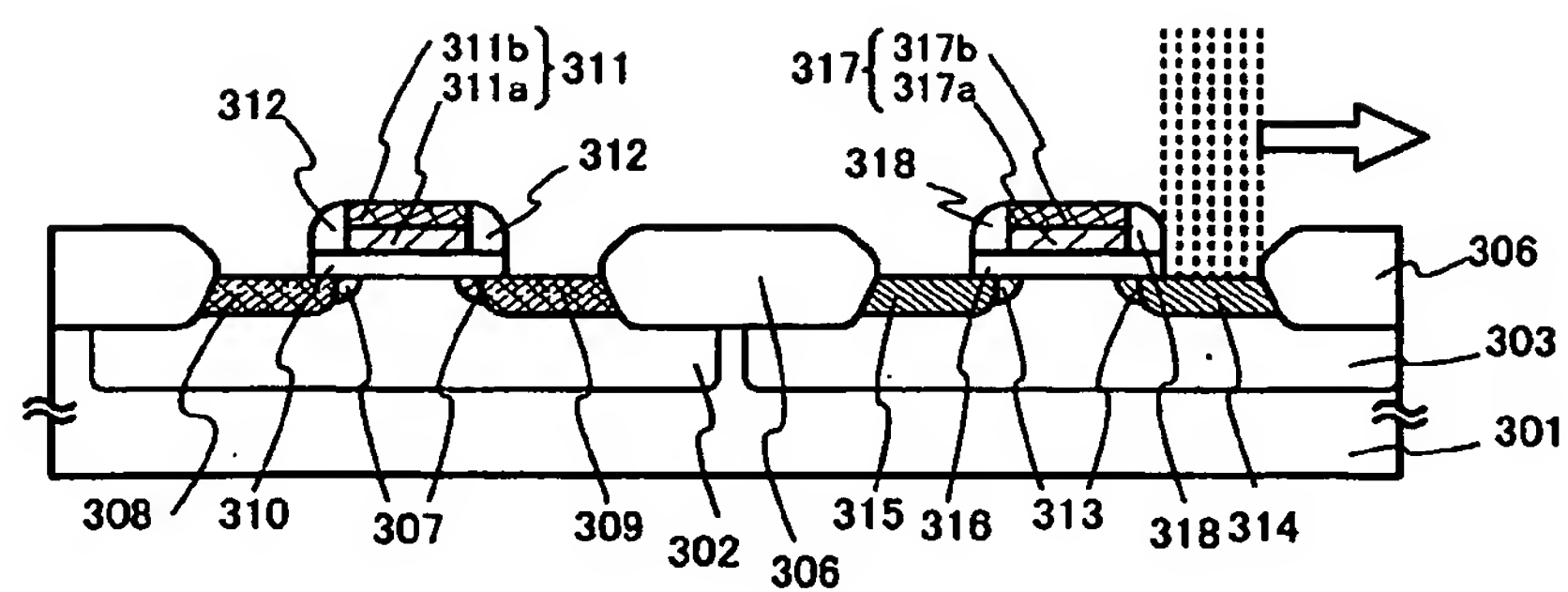


FIG. 3A

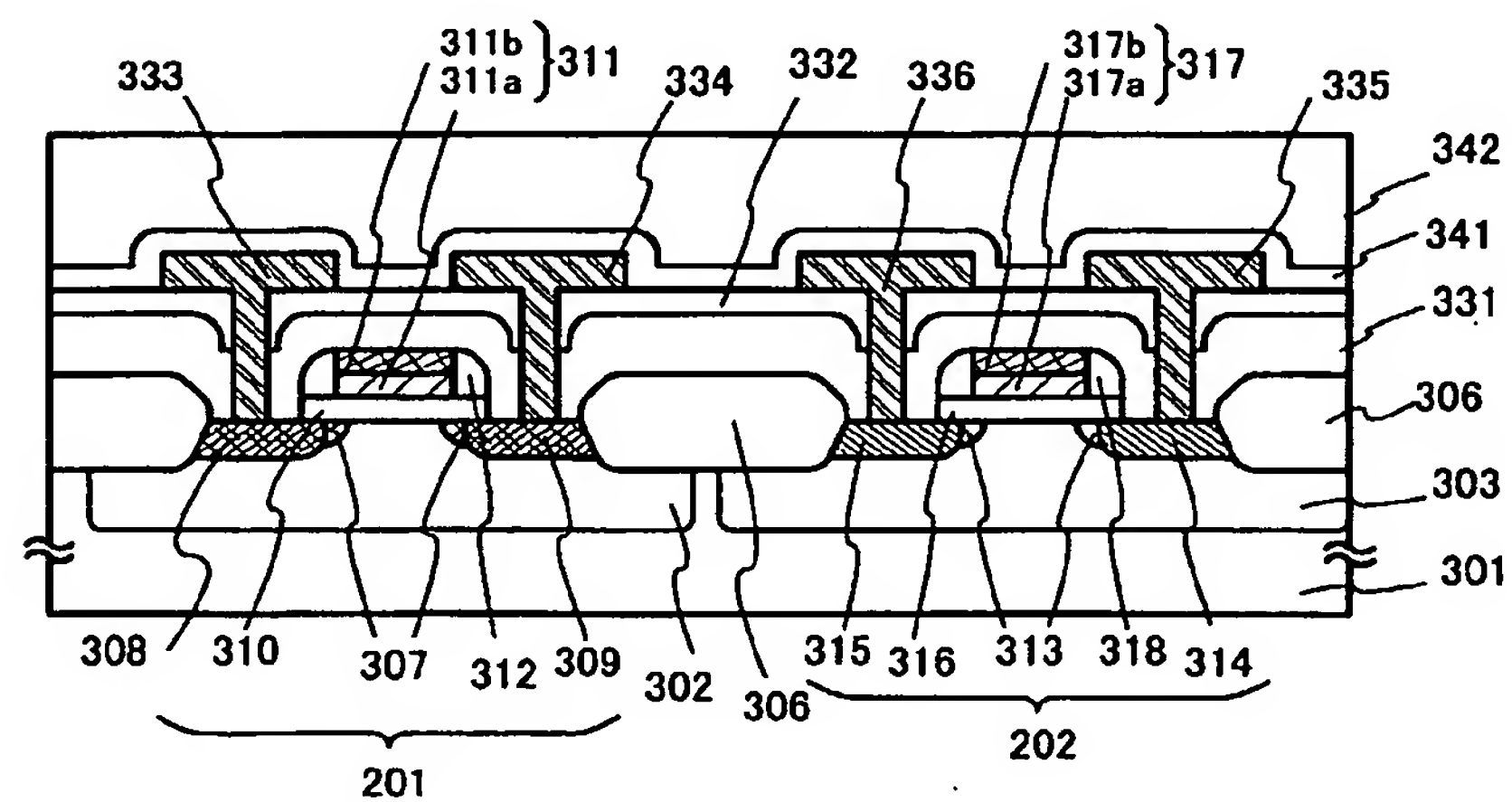


FIG. 3B

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FIG. 4A

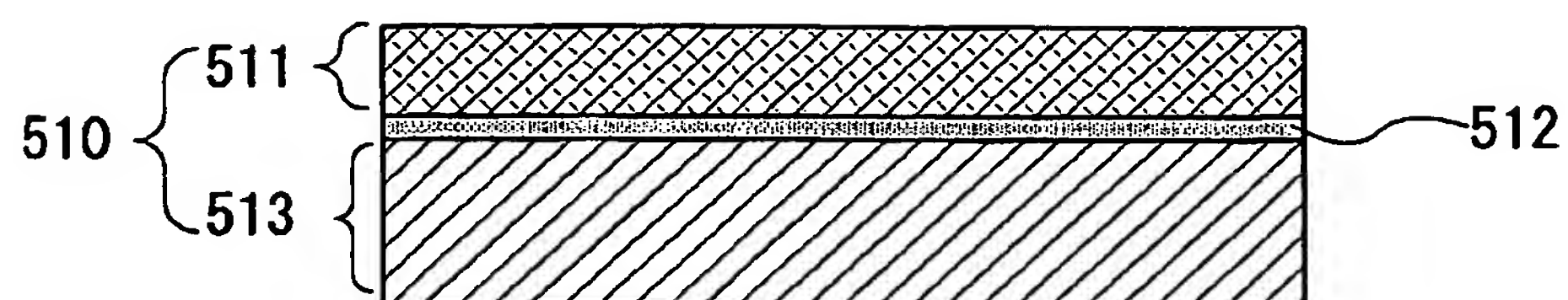


FIG. 4B

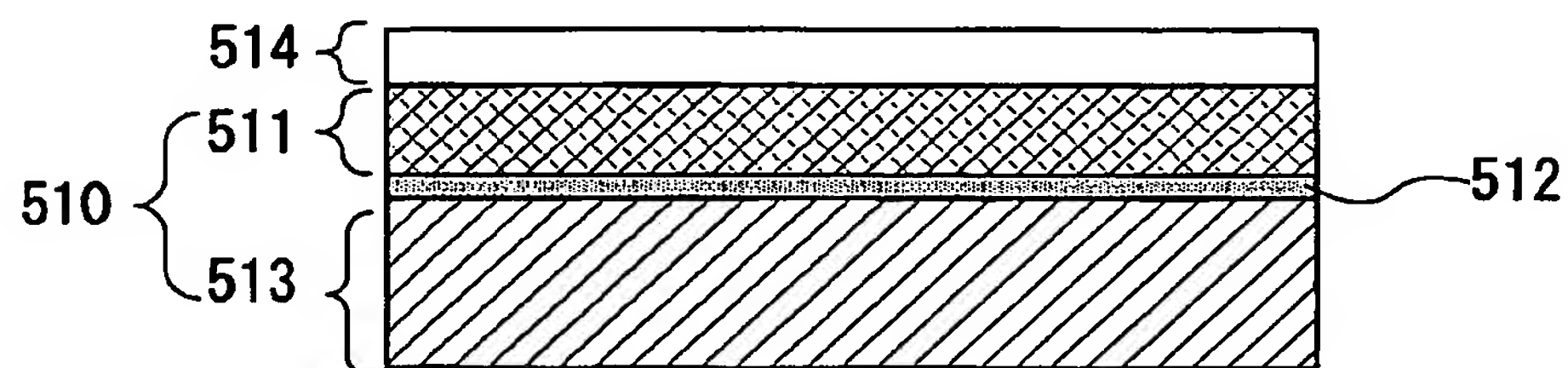


FIG. 4C

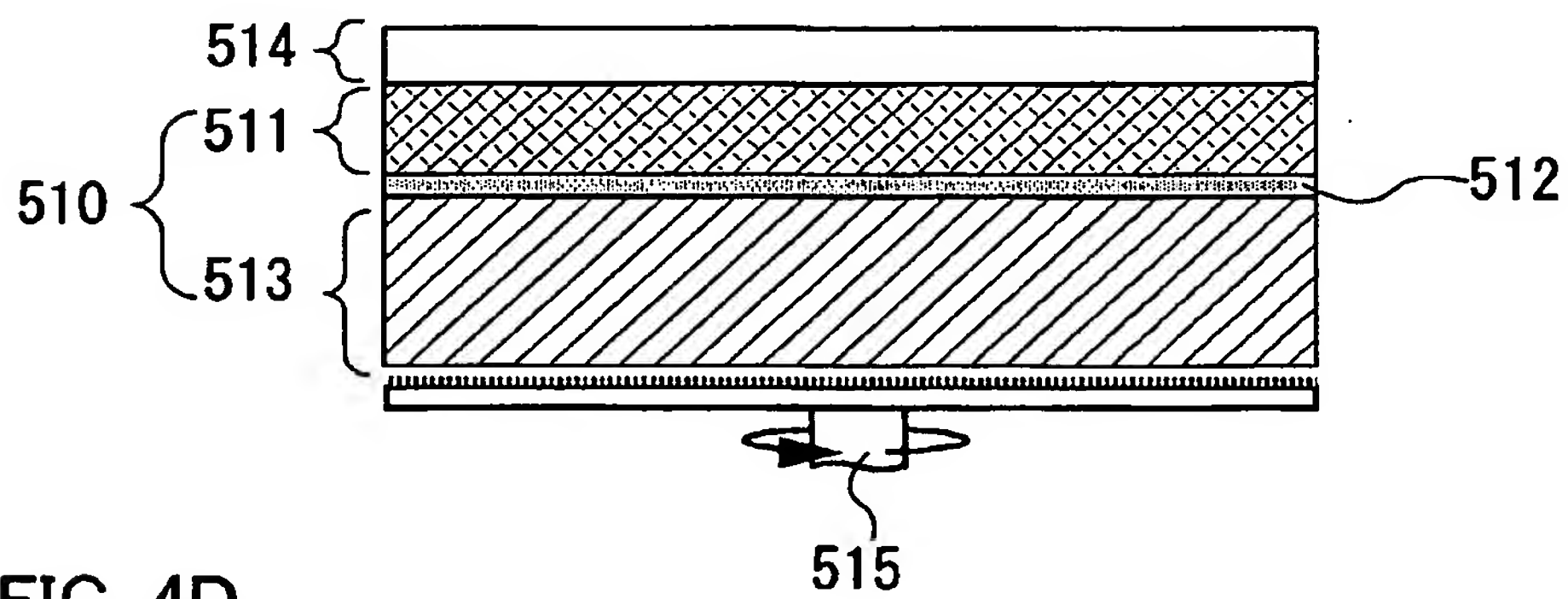
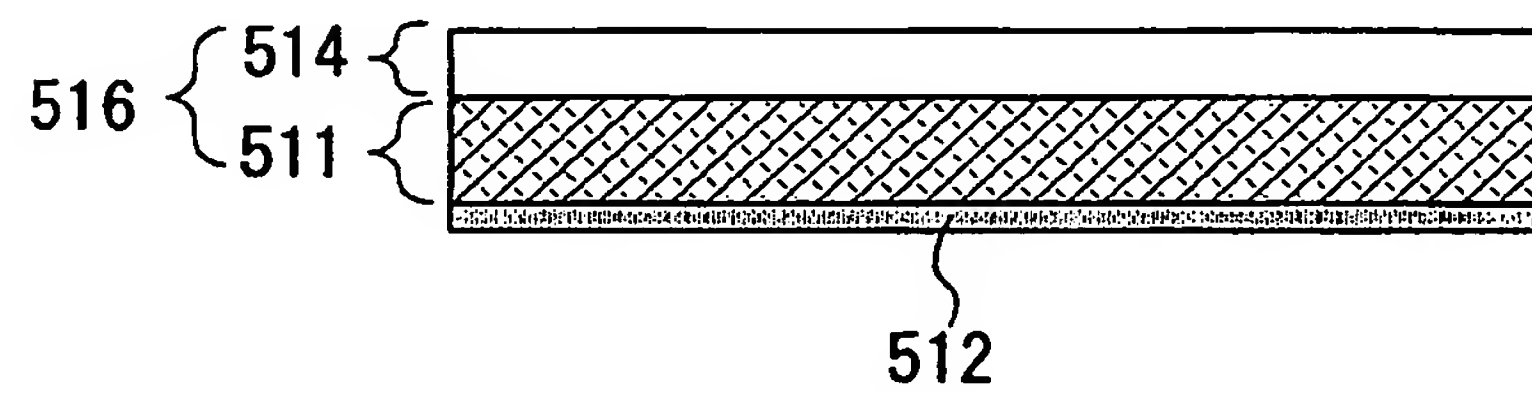


FIG. 4D



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FIG. 5A

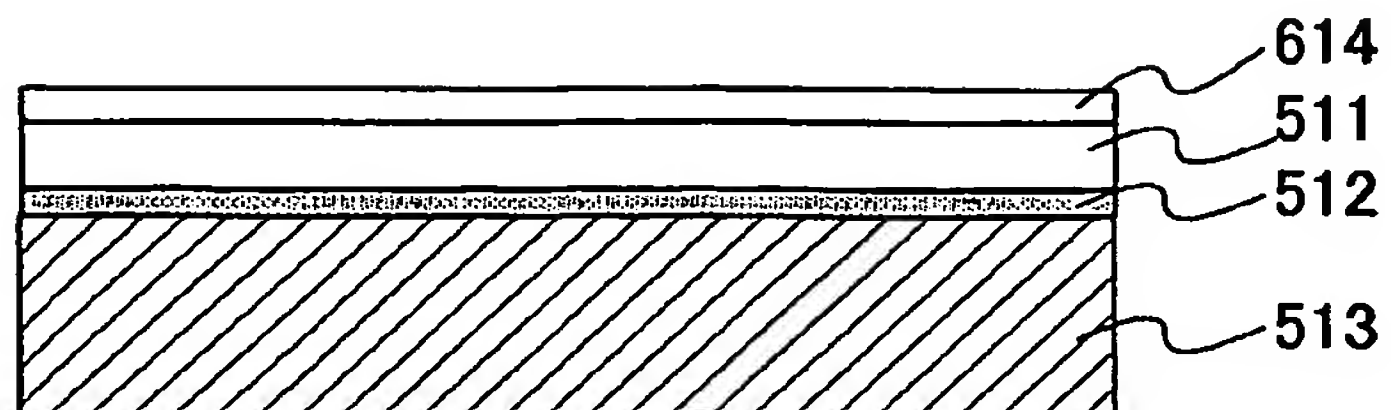


FIG. 5B

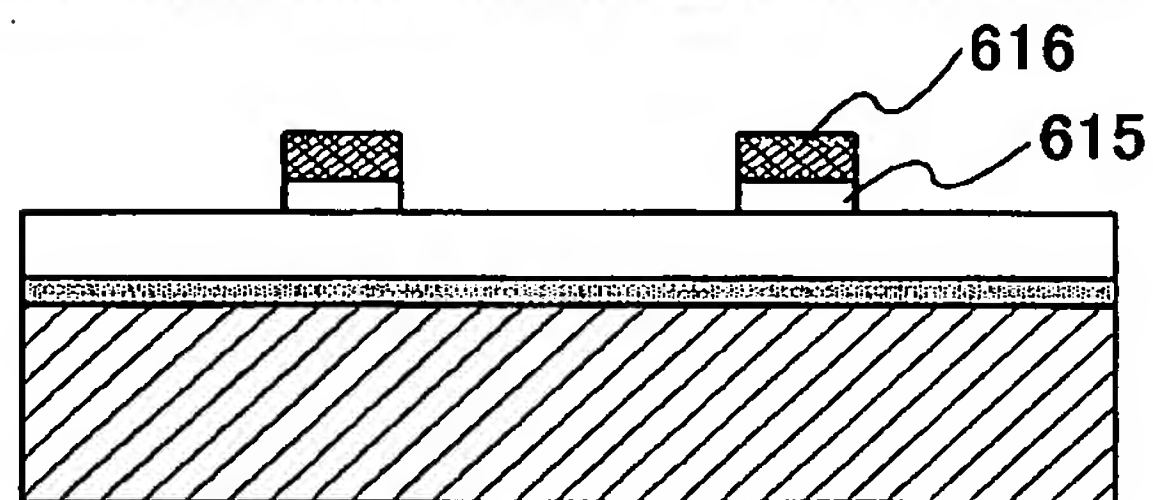


FIG. 5C

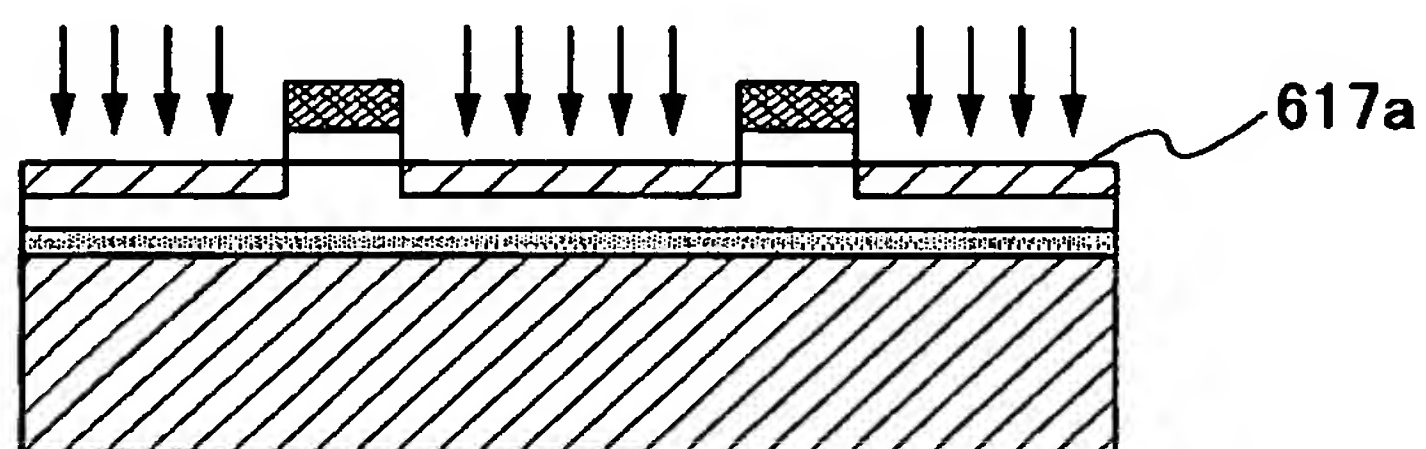


FIG. 5D

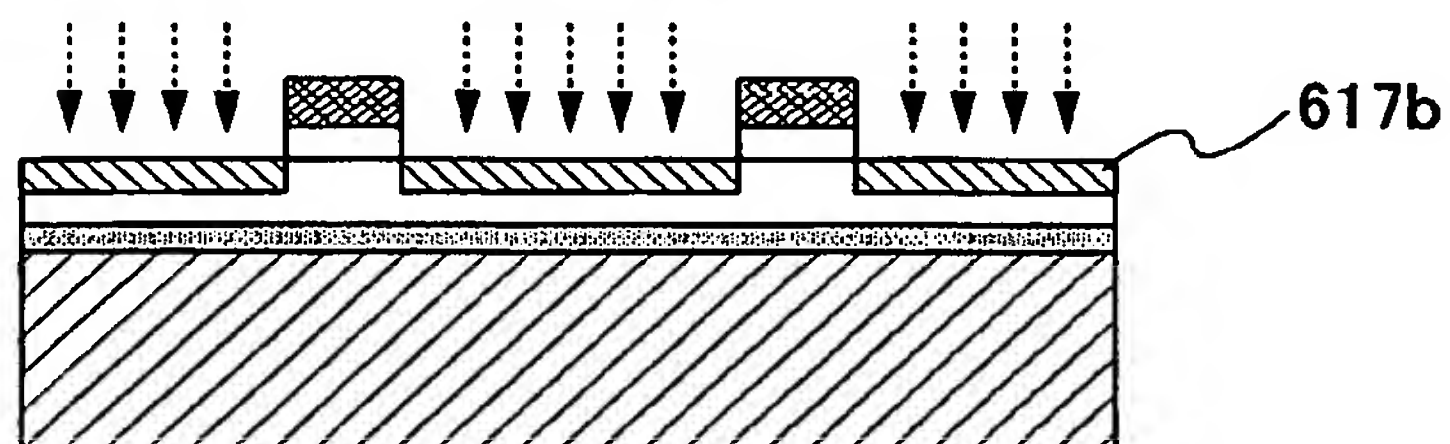


FIG. 5E

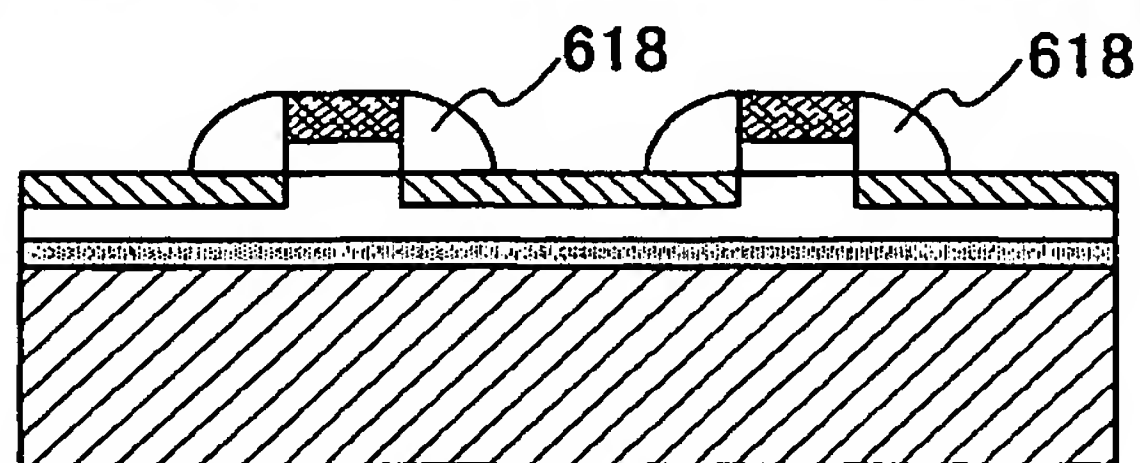
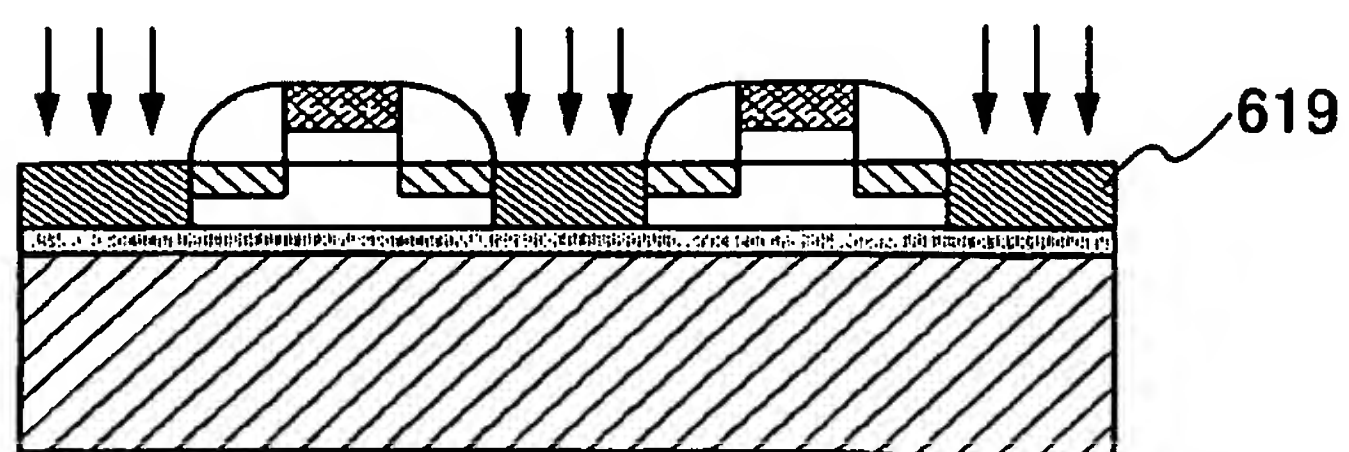


FIG. 5F



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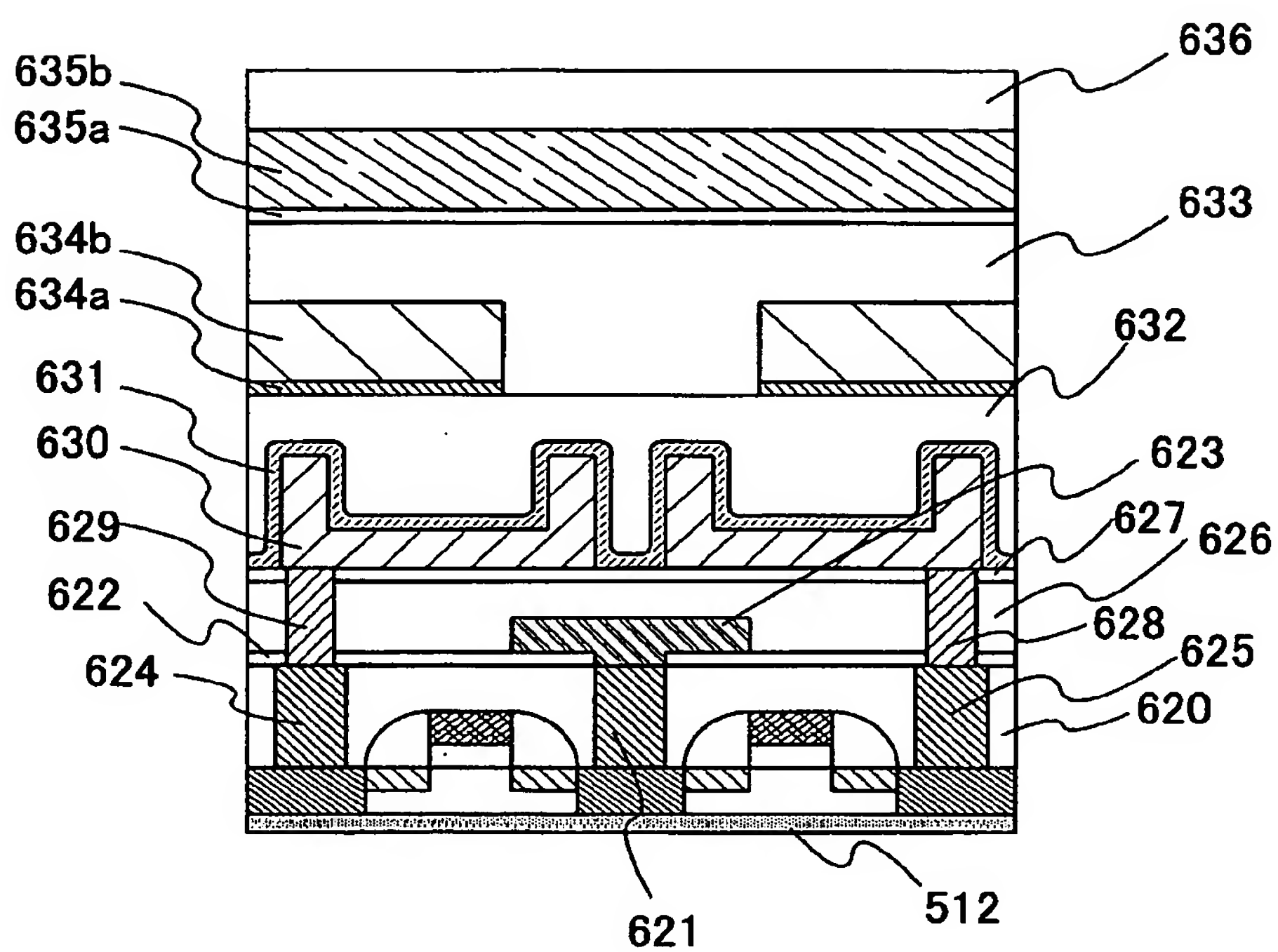


FIG. 6

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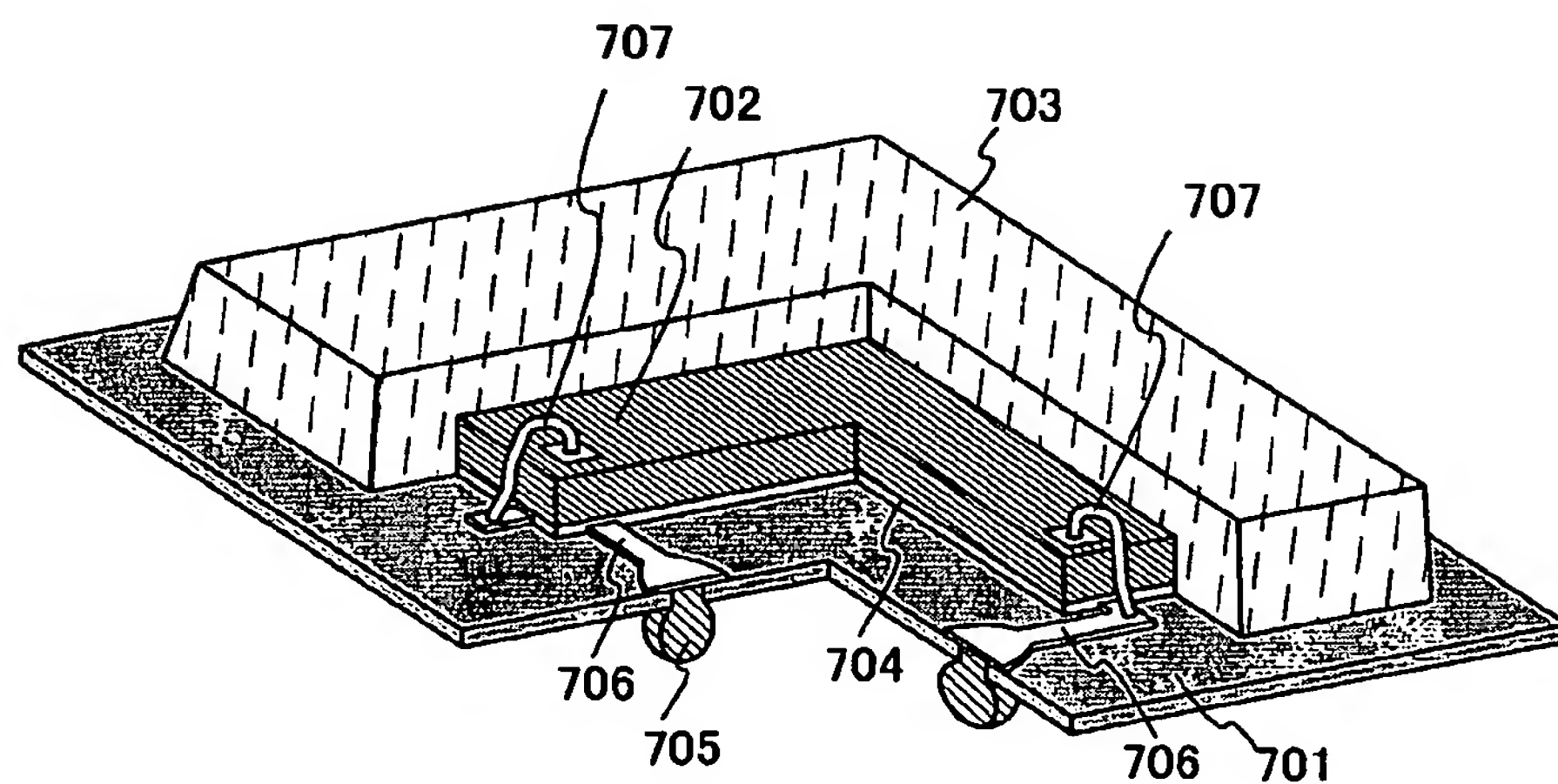


FIG. 7

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FIG. 8A

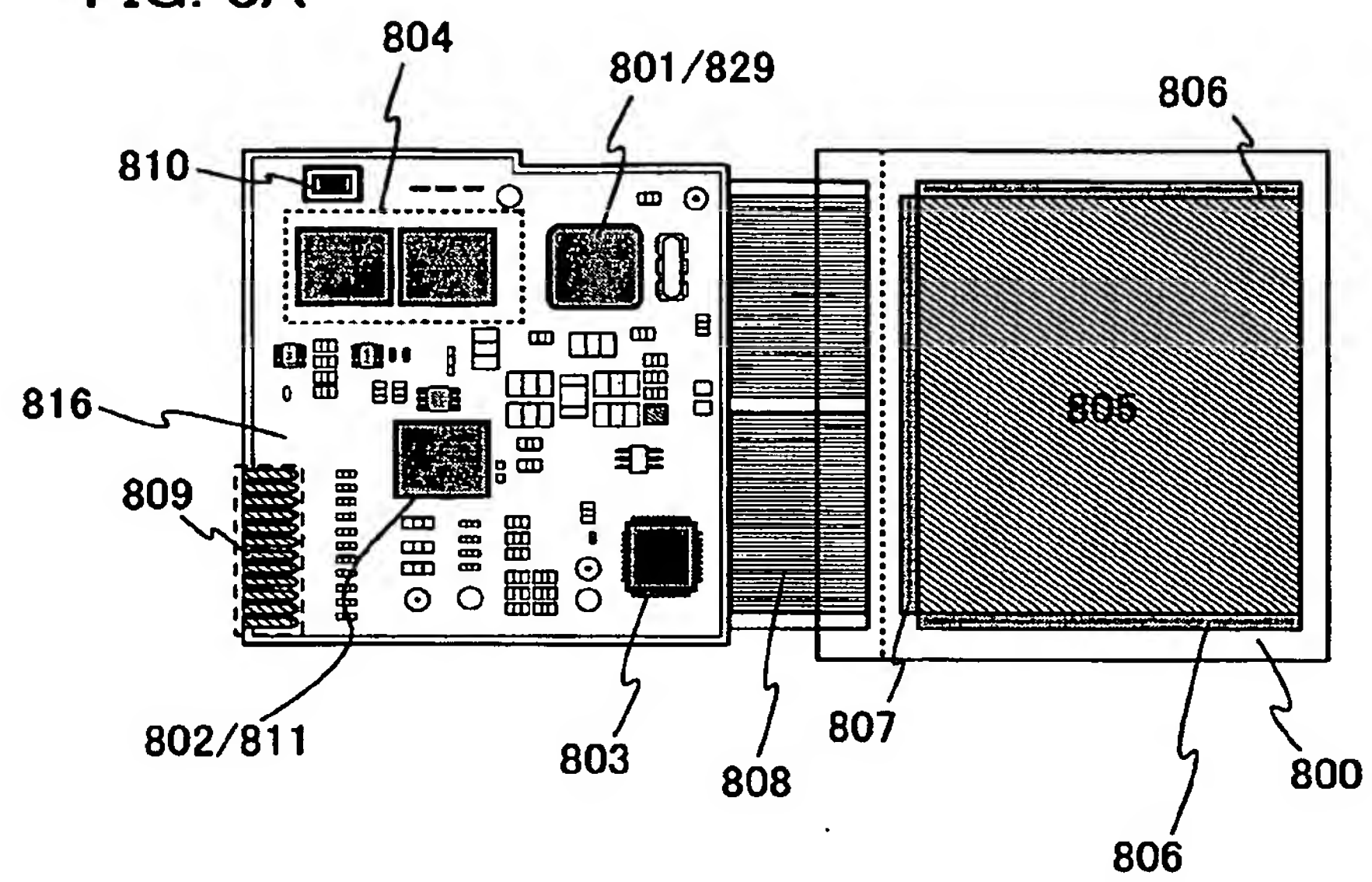
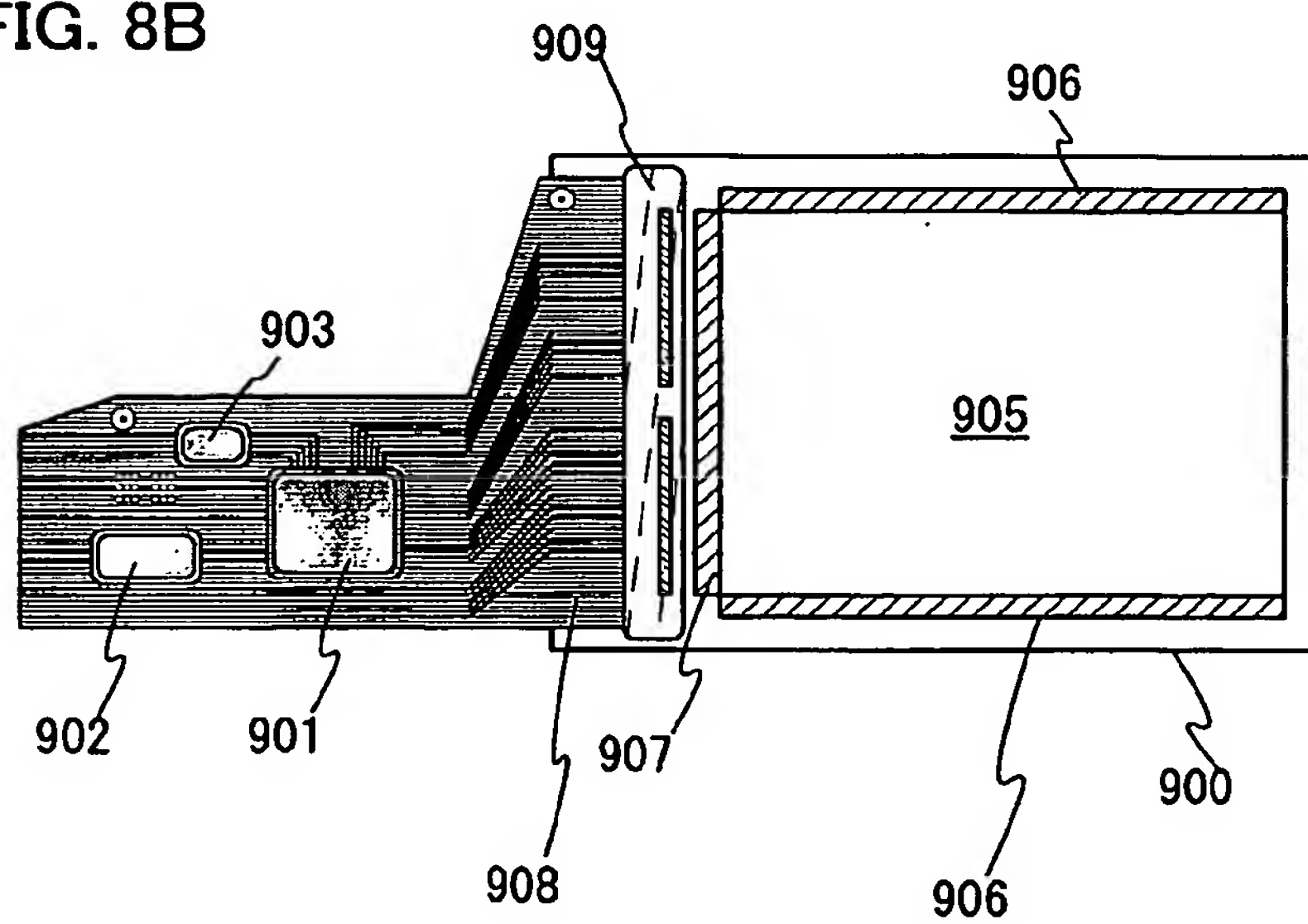


FIG. 8B



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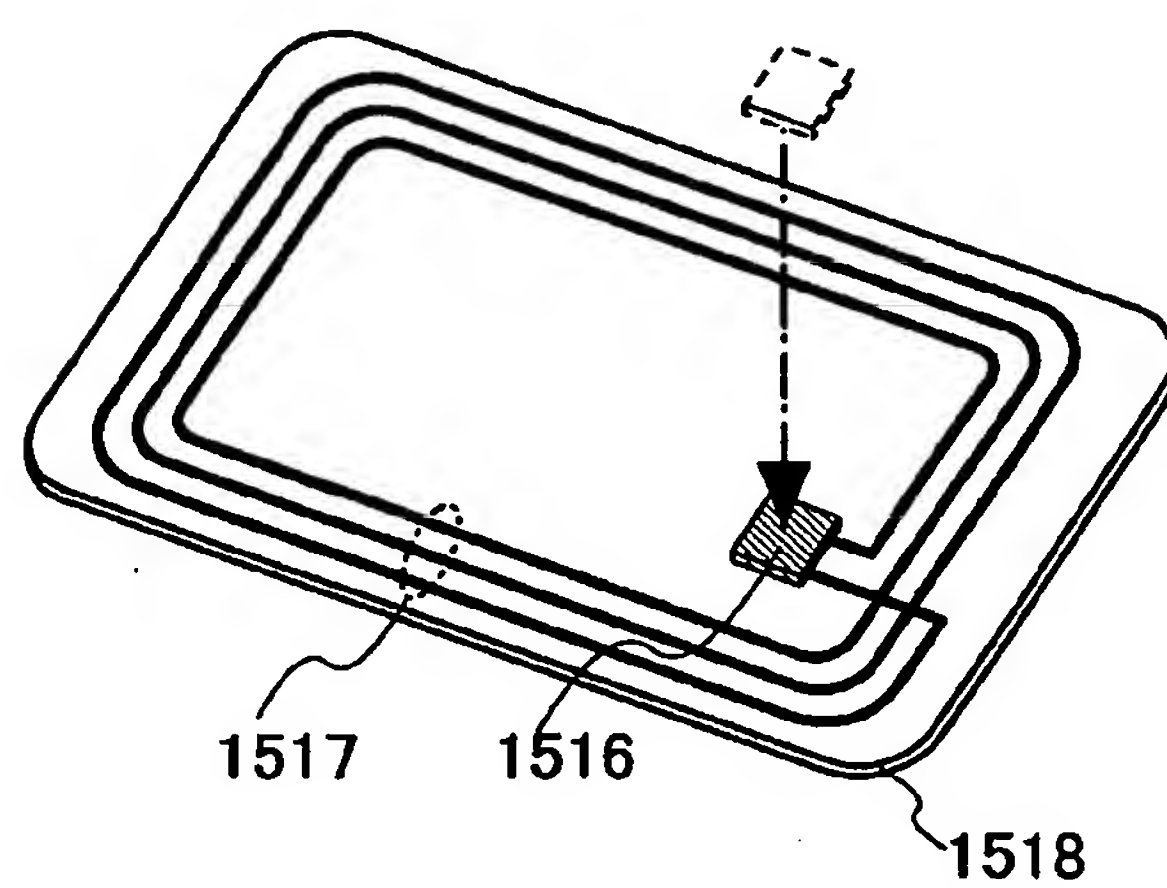


FIG. 9

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FIG. 10A

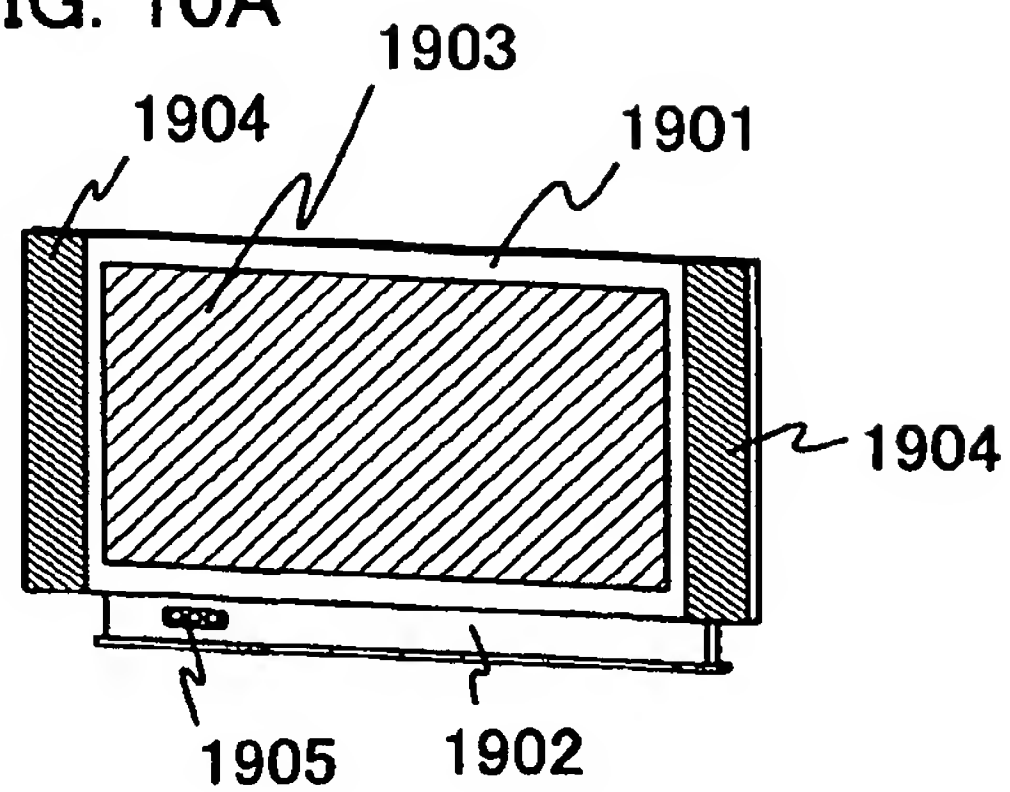


FIG. 10B

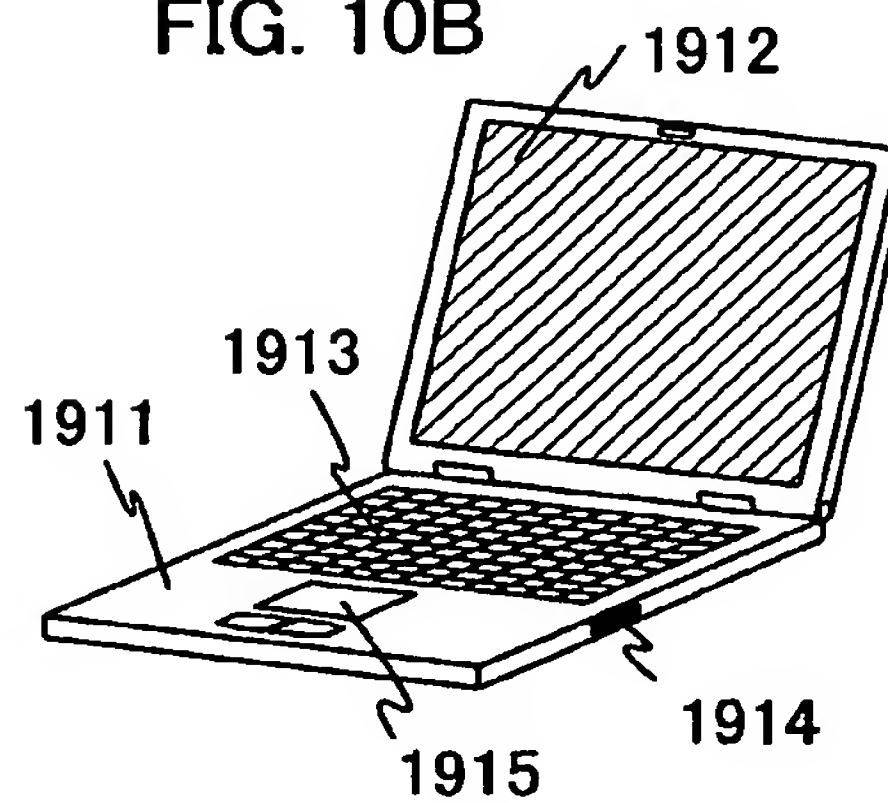


FIG. 10C

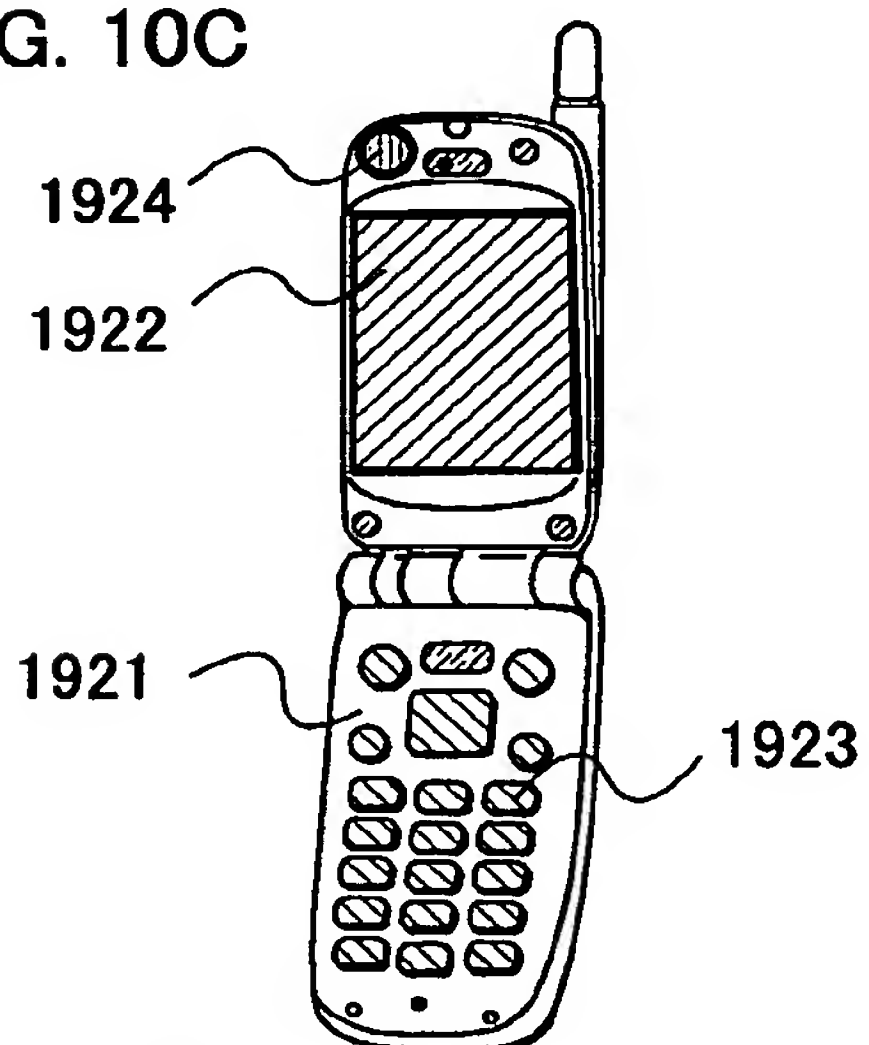


FIG. 10D

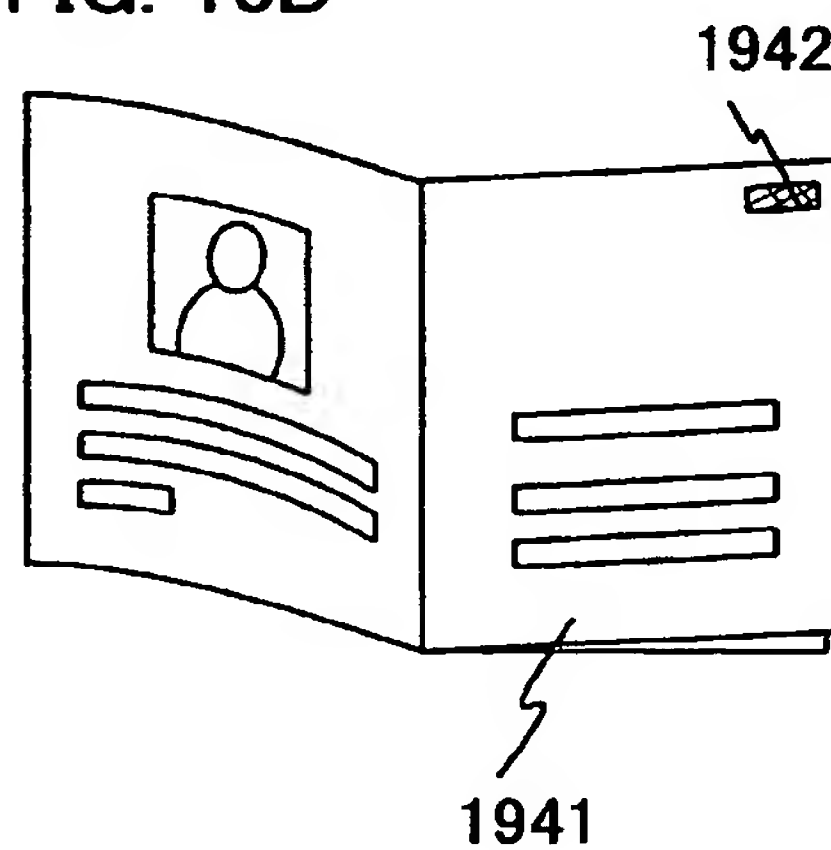
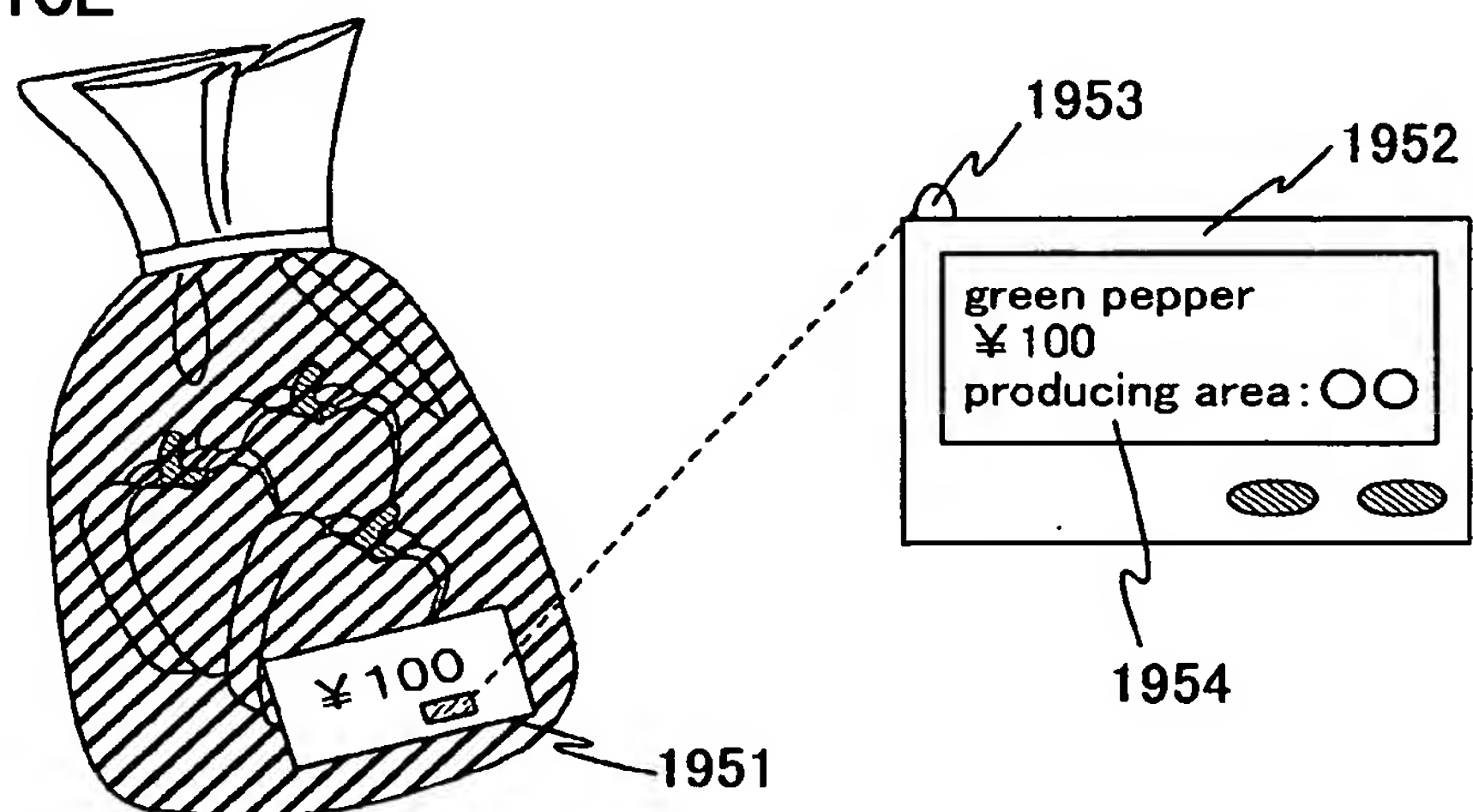


FIG. 10E



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EXPLANATION OF REFERENCE

101: laser oscillator, 102: slit, 103: mirror, 104: first cylindrical lens, 105: second cylindrical lens, 106: semiconductor substrate, 107: substrate fixing stage, 108: X stage, 109: Y stage, 110: laser beam, 111: beam irradiation region, 201: p-channel FET, 202: n-channel FET, 301: substrate, 302: n-well, 303: p-well, 306: field oxide film, 307: extension region, 308: source region, 309: drain region, 310: gate insulating film, 311: gate electrode, 311a: polysilicon layer, 311b: silicide layer, 312: sidewall, 313: extension region, 314: source region, 315: drain region, 316: gate insulating film, 317: gate electrode, 317a: polysilicon layer, 317b: silicide layer, 318: sidewall, 331: first interlayer insulating film, 332: second interlayer insulating film, 333: source electrode, 334: drain electrode, 335: source electrode, 336: drain electrode, 341: passivation film, 342: third interlayer insulating film, 510: SIMOX substrate, 511: first single-crystal semiconductor layer, 512: insulating layer, 513: second single-crystal semiconductor layer, 514: layer including second element, 515: grinding and polishing apparatus, 516: semiconductor device, 614: inorganic insulating film, 615: gate insulating film, 616: gate electrode, 617a: first impurity region, 617b: first impurity region, 618: sidewall, 619: second impurity region, 620: first silicon oxide film, 621: leading terminal, 622: second silicon oxide film, 623: bit line, 624: plug, 625: plug, 626: third silicon oxide film, 627: silicon nitride film, 628: plug, 629: plug, 630: electrode, 631: upper electrode, 632: first interlayer insulating film, 633: second interlayer insulating film, 634a: TiN film, 634b: film mainly containing Al, 635a: TiN film, 635b: film mainly containing Al, 636: final protective film, 701: lead frame, 702: chip, 703: mold resin layer, 704: adhesive agent, 705: solder ball, 706: wiring, 707: gold wire, 800: panel, 801: sound processing circuit, 802: memory, 803: power supply circuit, 804: transmitter-receiver circuit, 805: pixel portion, 806: scan line driver circuit, 807: signal line driver circuit, 808: FPC, 809: interface portion, 810: antenna port, 811: CPU, 816: printed wiring board, 829: controller, 900: panel, 901: controller, 902: CPU, 903: memory, 905: pixel portion, 906: scan line driver circuit, 907: signal line driver circuit, 908: FPC, 909:

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adhesive agent, 1516: IC chip, 1517: conductive layer, 1518: card-like substrate, 1901: casing, 1902: support, 1903: display portion, 1904: speaker portion, 1905: video input terminal, 1911: casing, 1912: display portion, 1913: keyboard, 1914: external connection port, 1915: pointing mouse, 1921: casing, 1922: display portion, 1923: operation key, 1924: sensor portion, 1941: passport, 1942: wireless IC tag, 1951: wireless IC tag, 1952: reader, 1953: antenna portion, 1954: display portion